Complete 10µs CMOS 12-Bit ADC

ABSOLUTE MAXIMUM RATINGS

V _{DD} to DGND	+7V Op
AGND to DGND	.3V I
AIN to AGND	
(Pins 17, 19-21) Digital Output Voltage to DGND0.3V, Vpp + 0	Po 3V
(pins 4-11, 13-16, 18, 22)	Le

perating Temperature Ranges
MAX172XC 0°C to +70°C
MAX172XE
MAX172XM
storage Temperature Range65°C to +160°C
Power Dissipation (any Package) to +75°C 1000mW
Derates Above +75°C by 10mW/°C
ead Temperature (Soldering 10 seconds) +300°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions above those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum ratings conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS (V_{DD} = +5V ± 5%, V_{SS} = -12V or -15V ± 5%; Slow Memory Mode; T_A = T_{MIN} to T_{MAX} unless otherwise noted, f_{CLK} = 1.25MHz.)

22A 22AC/AE 22AM 22B 22B 22B 22A	$T_A = 25^{\circ}C$ tic Over Temp. $T_A = 25^{\circ}C$ $T_A = T_{MIN}$ to T_{MAX}	12		+ 1/2 + 1/2 + 3/4	Bits	
2AC/AE 2AM 2B nteed Monoton 2B 2A	ic Over Temp. T₄ = 25°C	12		± 1/2 ± 3/4	<u>+</u>	
2AC/AE 2AM 2B nteed Monoton 2B 2A	ic Over Temp. T₄ = 25°C		······································	± 1/2 ± 3/4	LSB	
22AM 22B 1teed Monoton 22B 22A	ic Over Temp. T₄ = 25°C			+3/4	LSB	
2B 2A	T₄ = 25° C			±1		
2A				+1	LSB	
	A MIN ** MAX			±4 ±6	LSB	
	$T_A = 25^{\circ}C$ $T_A = T_{MIN}$ to T_{MAX}			±3 ±4		
'2B	T _A = 25°C			+ 15		
'2A	T _A = 25°C			+ 10	LSB	
	· · · · ·			+ 45	ppm/°(
		0		5	V	
0V to +5V				3.5	rnA	
5°C	-5.2	-5.25	-5.3	V		
			40		ppm/°	
6)				500	μA	
		-				
D, HBEN, CLK			0.8	V		
D, HBEN, CLK	2.4			V		
D, HBEN, CLK			10	pF		
D, HBEN	VIN = 0 to V _{DD}			+ 10 + 20	μA	
0/8, BUSY, CL	l		0.4	V		
0/8, BUSY, CL	4			V		
0/8 V = = $0V$	<u> </u>		+ 10	μA		
				15	pF	
Y	10/8, V _{OUT} = 0V	00/8, V _{OUT} = 0V to V _{DD}	10/8, V _{OUT} = 0V to V _{DD}	10/8, V _{OUT} = 0V to V _{DD}		

MAX172

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ELECTRICAL CHARACTERISTICS (Continued) $(V_{DD} = +5V \pm 5\%, V_{SS} = -12V \text{ or } -15V \pm 5\%$; Slow Memory Mode; $T_A = T_{MIN}$ to T_{MAX} unless otherwise noted, $f_{CLK} = 1.25MHz$.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
CONVERSION TIME						
MAX172	t _{CONV}	Synchronous (12.5 clock cycles) Asynchronous (12 to 13 clock cycles)			10 10.4	μs
POWER SUPPLY REJECT	ION					
V _{DD} Only		FS Change, V_{SS} = -15V, V_{DD} = 4.75V to 5.25V		±1/2		LSB
V _{SS} Only		FS Change, V_{DD} = 5V, V_{SS} = -5% to +5%		±1/8		LSB
POWER REQUIREMENTS	,,,					
V _{DD}		±5% for Specified Performance 5				V V
V _{SS} (Note 8)		±5% for Specified Performance		5	V	
		$\overline{CS} = \overline{RD} = V_{DD}$, AIN = 5V		5	7	mA
I _{SS}		$\overline{CS} = \overline{RD} = V_{DD}$, AIN = 5V		8	12	mA
Power Dissipation		V _{DD} = +5V, V _{SS} = -15V		145	215	mW

MAX172

Note 1: Typical change over temp is +1 LSB. Note 2: $V_{DD} = +5V$, $V_{SS} = -15V$, FS = +5.000V, Ideal last code transition = FS - 3/2LSB. Note 3: Full Scale TC = Δ FS/ Δ T, where Δ FS is full scale change from T_A = 25°C to T_{MIN} or T_{MAX}.

Note 3: Full scale TC = $\Delta F_{S/\Delta}$, where ΔF_{S} is the scale change from $T_A = 25^{\circ}$ C to T_{MIN} or T_{MAX} Note 4: Includes internal reference drift. Note 5: V_{REF} TC = $\Delta V_{REF}/\Delta T$, where ΔV_{REF} is reference voltage change from $T_A = 25^{\circ}$ C to T_{MIN} or T_{MAX} Note 6: Output current should not change during conversion. Note 7: Guaranteed by design, not subject to test. Note 8: Functional operation at $V_{SS} = -12V + 5\%$ is guaranteed by testing offset error and full scale error.

TIMING CHARACTERISTICS (Note 9)

(V_{DD} = +5V, V_{SS} = -12V or -15V; T_A = T_{MIN} to T_{MAX} unless otherwise noted.)

PARAMETER	SYMBOL	CONDITIONS	T _A = 25°C			MAX172C/E		MAX172M		UNITS
			MIN	ТҮР	MAX	MIN	MAX	MIN	MAX	UNITS
CS to RD Setup Time	t ₁		0			0		0		ns
RD to BUSY Delay	t ₂	C _L = 50pF		90	190		230		270	ns
Data Access Time (Note 10)	t ₃	C _L = 20pF C _L = 100pF		60 70	90 125		110 150		120 170	ns
RD Pulse Width	t ₄		t ₃			t ₃		t ₃		
CS to RD Hold Time	t ₅		0			0		0		ns
Data Setup Time After BUSY Note (10)	t ₆				70		90		100	ns
Bus Relinquish Time (Note 11)	t ₇		20		75	20	85	20	90	ns
HBEN to RD Setup Time	t ₈		0			0		0		ns
HBEN to RD Hold Time	t ₉		0			0		0		ns
Delay Between Read Operations	t ₁₀	_	200			200		200		ns

Timing specifications are sample tested at 25°C to ensure compliance. All input control signals are specified with Note 9: t_r = t_r = 5ns (10% to 90% of +5V) and timed from a voltage level of +1.6V. Note 10: t_3 and t_6 are measured with the load circuits of Figure 1 and defined as the time required for an output to cross

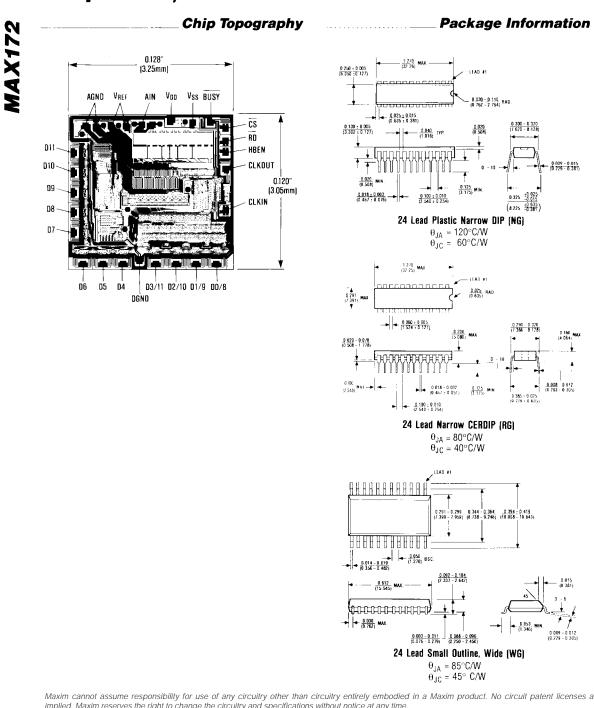
0.8V or 2.4V.

Note 11: t₇ is defined as the time required for the data lines to change 0.5V when loaded with the circuits of Figure 2.

For additional information on using the MAX172 please refer to MAX162 data sheet.

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